

**Notice of References Cited**

Application/Control No.

10/147,319

Applicant(s)/Patent Under Reexamination  
DWILINSKI ET AL.

Examiner

Matthew J Song

Art Unit

1765

Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,177,057	01-2001	Purdy, Andrew P.	423/409
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	WO 01/024921A1	04-2001	WIPO	D'Evelyn et al	B01J 3/06
	O	EP 1088914 A1	04-2001	European Patent	MOTOKI et al.	C30B 25/02
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Mao et al. "New concept technology pressure variation liquid phase epitaxy", SPIE Photonics Taiwan Conference Proceeding July 2000, pg 1-12.
	V	Ketchum et al. "Crystal growth of gallium nitride in supercritical ammonia", Journal of Crystal Growth 222 (2001) pp 431-434.
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

**Notice of References Cited**

Application/Control No.

10/147,318

Applicant(s)/Patent Under  
Reexamination  
DWILINSKI ET AL.

Examiner

Stephen J Stein

Art. Unit

1775

Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5,928,421	07-1999	Yuri et al.	117/97
	B	US-6,156,581	12-2000	Vaudo et al.	438/22
	C	US-2001/0008656	07-2001	TISCHLER et al.	428/34.1
	D	US-2001/0022154	09-2001	Cho et al.	117/2
	E	US-6,372,041	04-2002	Cho et al.	117/84
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	EP 0711853 B1	09-1999	EPO	Togawa et al.	---
	O	JP410070079A	03-1998	JPO	Yuri et al.	---
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Melnik et al. "Properties of Free-Standing GaN Bulk Crystals Grown by HPVE", Mat. Res. Soc. Symp. Proc. Vol. 482 (1998) pp. 269-274.
	V	Balkas et al. "Growth of Bulk AlN and GaN Single Crystals by Sublimation", Mat. Res. Soc. Symp. Proc. Vol. 449 (1997) pp 41-46.
	W	Porowski et al. "Bulk and Homoepitaxial GaN-Growth and Characterisation", Journal of Crystal Growth, 189/190 (1998) pp. 153-158.
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
 Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.